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**\*BIBDATASHEET\***

CONFIRMATION NO. 2008

Bib Data Sheet

SERIAL NUMBER 10/034,895	FILING DATE 12/28/2001  RULE	CLASS 428	GROUP ART UNIT 1773	ATTORNEY DOCKET NO. YAMAP0718USA
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## \*\* CONTINUING DATA \*\*\*\*\*

This application is a DIV of 09/596,116 06/16/2000 PAT 6,436,526

## \*\* FOREIGN APPLICATIONS \*\*\*\*\*

JAPAN 11-170486 06/17/1999

JAPAN 11-352962 12/13/1999

## IF REQUIRED, FOREIGN FILING LICENSE GRANTED

\*\* 02/04/2002

Foreign Priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no	STATE OR COUNTRY JAPAN	SHEETS DRAWING 16	TOTAL CLAIMS 54	INDEPENDENT CLAIMS 14
35 USC 119 (a-d) conditions met <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance				
Verified and Acknowledged Examiner's Signature _____ Initials _____				

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## TITLE

Magneto-resistance effect element magneto-resistance effect memory cell, MRAM, and method for performing information write to or read from the magneto-resistance effect memory cell

☐ All Fees

☐ 1.16 Fees ( Filing )